

# **isc Silicon NPN Darlington Power Transistor**

2SD1566

### **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 100V(Min)
- · Collector-Emitter Saturation Voltage-
  - :  $V_{CE(sat)}$ = 1.5V(Max) @ $I_C$ = 10A
- · Fast Switching Speed
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

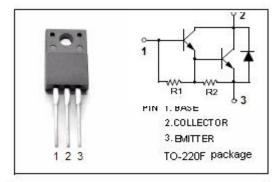


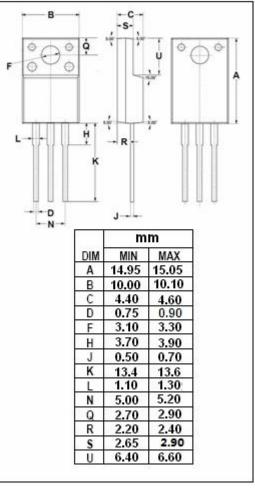
## **APPLICATIONS**

· Designed for high current switching applications.

## ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
Vсво	Collector-Base Voltage	150	V
V <sub>CEO</sub>	Collector-Emitter Voltage	100	V
V <sub>EBO</sub>	Emitter-Base Voltage	8	V
lc	Collector Current-Continuous	10	Α
I <sub>B</sub>	Base Current-Continuous	1	Α
Pc	Collector Power Dissipation @ T <sub>C</sub> =25℃ 60		W
TJ	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C







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### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}$ =25°C unless otherwise specified

10-23 C uniess otherwise specified									
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	100			V			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 25mA			1.5	V			
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 25mA			2.0	V			
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 150V; I <sub>E</sub> = 0			10	μА			
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 8V; I <sub>C</sub> = 0			5	mA			
h <sub>FE</sub>	DC Current Gain	Ic= 10A; V <sub>CE</sub> = 2V	1000						
V <sub>ECF</sub>	C-E Diode Forward Voltage	I <sub>F</sub> = 10A			3.0	V			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V		20		MHz			
Switching times									
t <sub>on</sub>	Turn-on Time				1.0	μ \$			
t <sub>stg</sub>	Storage Time	I <sub>B1</sub> = I <sub>B2</sub> = 25mA; R <sub>L</sub> = 5 Ω; V <sub>CC</sub> = 50V			5.0	μ <b>S</b>			
t <sub>f</sub>	Fall Time				2.0	μS			

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